

# 5A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER **POWERMITE**® 3

#### **Features**

- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Reverse Breakdown Voltage
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- Plastic Material: UL Flammability Classification Rating 94V-0

### **Mechanical Data**

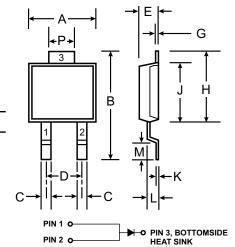
Case: POWERMITE®3 Molded Plastic

Terminals: Solderable per MIL-STD-202,

Method 208

Polarity: See DiagramMarking: See sheet 3

Weight: 0.072 grams (approx.)



4.09 Α 4.03 6.40 В 6.61 С .889 NOM D 1.83 NOM 1.10 Ε 1.14 G .178 NOM Н 5.01 5.17 J 4.37 4.43 Κ .178 NOM L .71 .77 .36 .46 М 1.73 1.83 All Dimensions in mm

**POWERMITE®3** 

Min

Max

Dim

Note: Pins 1 & 2 must be electrically connected at the printed circuit board.

## **Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

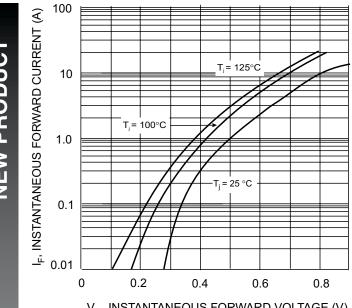
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	70	V
Average Rectified Output Current (See also figure 5)	Io	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave Superimposed on Rated Load (JEDEC Method) @T <sub>C</sub> = 80°C	I <sub>FSM</sub>	100	А
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	1.2	°C/W
Typical Thermal Resistance Junction to Soldering Point	R <sub>0</sub> JS	2.7	°C/W
Operating Temperature Range	Tj	-65 to +125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C

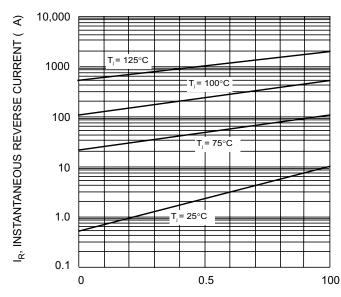
#### **Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 1)	V <sub>(BR)R</sub>	100	_	_	V	I <sub>R</sub> = 0.2mA
Forward Voltage (Note 1)	V <sub>FM</sub>		0.75 0.58 0.84 0.67	0.81 0.64 0.90 0.73	V	$\begin{array}{lll} I_F = 5A, \ T_j = & 25^{\circ}C \\ I_F = 5A, \ T_j = & 125^{\circ}C \\ I_F = 10A, \ T_j = & 25^{\circ}C \\ I_F = & 10A, \ T_j = & 125^{\circ}C \end{array}$
Peak Reverse Current (Note 1)	I <sub>RM</sub>		0.015 2	0.2 100	mA	$T_j = 25^{\circ}C$ , $V_R = 100V$ $T_j = 125^{\circ}C$ , $V_R = 100V$

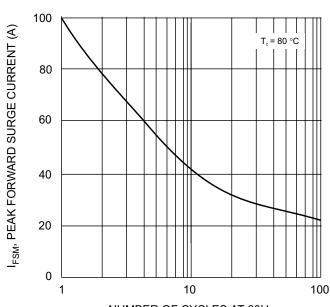
Notes: 1. Short duration test pulse used to minimize self-heating effect.



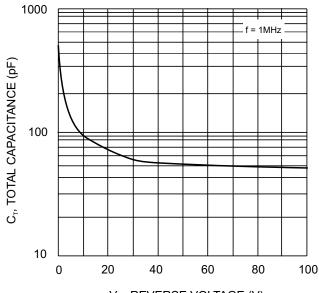
V<sub>F,</sub> INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 1 Typical Forward Characteristics



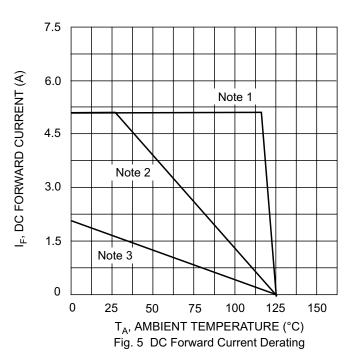
 ${
m V_R},$  INSTANTANEOUS REVERSE VOLTAGE (V) Fig. 2 Typical Reverse Characteristics

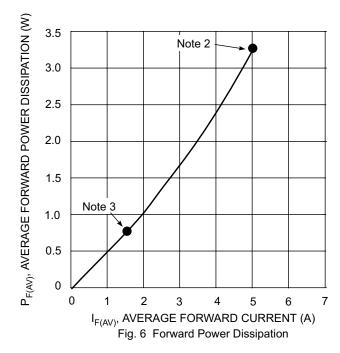


NUMBER OF CYCLES AT 60Hz
Fig. 3 Max Non-Repetitive Peak forward Surge Current



V<sub>R</sub>, REVERSE VOLTAGE (V) Fig. 4 Typical Capacitance vs. Reverse Voltage





Notes:

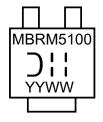
- 1.  $T_A = T_{SOLDERING\ POINT}$ ,  $R_{\theta JS} = 2.7^{\circ}C/W$ ,  $R_{\theta SA} = 0^{\circ}C/W$ .
- 2. Device mounted on GETEK substrate, 2"x2", 2 oz. copper, double-sided, cathode pad dimensions 0.75" x 1.0", anode pad dimensions 0.25" x 1.0".  $R_{\theta JA}$  in range of 20-40°C/W.
- Device mounted on FR-4 substrate, 2"x2", 2 oz. copper, single-sided, pad layout as per Diodes Inc. suggested pad layout document AP02001 which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. R<sub>θJA</sub> in range of 100-140°C/W.

## **Ordering Information** (Note 4)

Device	Packaging	Shipping
MBRM5100-13	POWERMITE®3	5000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



MBRM5100 = Product type marking code

O!! = Manufacturers' code marking

YYWW = Date code marking

YY = Last digit of year ex: 2 for 2002

WW = Week code 01 to 52

**POWERMITE** is a registered trademark of Microsemi Corporation.